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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TN	A1	5,332,697	07/26/1994	Smith et al.	437 438	242 202	10/16/1991
TN	A2	6,090,666	07/18/2000	Ueda et al.	438	257	09/30/1998

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TN	A3	EP 0 779 666 A2	06/18/1997	Europe				
TN	A4	EP 0 942 459 A1	09/15/1999	Europe				
TN	A5	11-111-867	04/23/1999	Japan				✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TN	A6	Patent Abstracts of Japan, Publication No. 1111867, Publication Date 04/23/1999, 1 page
TN	A7	"Drastic Reduction of the Dislocation Density in GaN Films by Anti-Surfactant-Mediated Dot Formation", M. Takeuchi et al., Workbook, The Tenth International Conference on Matalorganic Vapor Phase Epitaxy, June 5-9, 2000, Sapporo, Japan, 3 pages

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